

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|------------------------------------|------------------|---------|------------------|
| L1 | 10 | (US-20060163605-\$).did. or (US-6001748-\$ or US-5668524-\$ or US-5766783-\$).did. or (WO-2005003414-\$ or WO-2004005216-\$).did. or (JP-04092866-\$ or JP-04092865-\$). did. or (WO-2004005216-\$ or WO-2005003414-\$).did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 06:34 |
| L2 | 1 | (rough roughness) and L1 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 06:34 |
| L3 | 71 | ((sintered with compact) same (rough roughness)) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:10 |
| L4 | 5 | ((sintered with compact) same (rough roughness)) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (specific adj resistance) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:10 |
| L5 | 1250 | (conduction adj via) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:27 |
| L6 | 36 | (conduction adj via) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:30 |

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| L7 | 23 | (conduction adj via) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (thin near3 film) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:42 |
| L8 | 50 | (substrate same (conduction with channel)) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (thin near3 film) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 08:42 |
| S1 | 78 | kenichiro.inv. and miyahara.inv. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/08/02 13:00 |
| S2 | 2 | ((("6001748") or ("5668524"))).PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2006/08/02 12:40 |
| S3 | 1 | ((thin adj film) with (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))) and ((sinter\$ adj compact) with (AlN (aluminum adj nitride))) and (hexagonal trogonal) and (optical with permeab\$) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/08/03 08:37 |
| S4 | 3 | (trigonal hexagonal) and (S1 S2 S3) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/08/02 15:17 |

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| S5 | 32 | ((thin adj film) with (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))) and (sinter\$ with (AlN (aluminum adj nitride))) and (hexagonal trogonal wurtzite) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/08/03 09:25 |
| S6 | 7 | (sintered with compact with ((optical visible light) near3 (permeab\$ transpar\$))) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/02/20 06:38 |